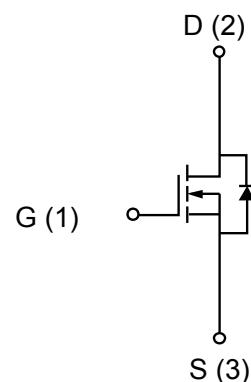


## Description

The MOSFET provide the best combination of fast switching, low on-resistance and cost-effectiveness.

MOSFET Product Summary		
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (mΩ)	I <sub>D</sub> (A)
30	8.3@V <sub>GS</sub> =10V	60



## Absolute maximum rating@25°C

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V <sub>DS</sub>	30	V
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Drain Current- Continuous(T <sub>J</sub> =150°C)*	I <sub>D</sub>	60	A
T <sub>A</sub> =70°C	I <sub>D</sub>	40	
Drain Current-Pulsed	I <sub>DM</sub>	100	A
Maximum Power Dissipation*	P <sub>D</sub>	40	W
T <sub>A</sub> =70°C	P <sub>D</sub>	25	
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to 150	°C
Thermal Resistance, Junction-to-Ambient *	R <sub>θJA</sub>	40	°C/W
Thermal Resistance, Junction-to-Case	R <sub>θJC</sub>	3.1	°C/W

\*The device mounted on 1in<sup>2</sup> FR4 board with 2 oz copper

## Electrical characteristics per line@25°C( unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
<b>Static</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$I_D = 250\mu A, V_{GS} = 0V$	30		-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 30V, V_{GS} = 0V$	-	-	1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{DS} = 0V, V_{GS} = \pm 20V$			$\pm 100$	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1		3	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS} = 4.5V, I_D = 15A$	-	14	18.5	$m\Omega$
		$V_{GS} = 10V, I_D = 30A$		8.3	10	
Drain-Source Diode Forward Voltage	$V_{SD}$	$V_{GS} = 0V, I_S = 20A$		0.87	1.5	V
Max. Diode Forward Current	$I_S$				20	A
<b>Dynamic</b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 15V, V_{GS} = 0V, f = 1.0MHz$		830		$pF$
Output Capacitance	$C_{oss}$			150		
Reverse Transfer Capacitance	$C_{rss}$			43		
Gate Resistance	$R_g$	$f = 1MHz$		1		$\Omega$
Total Gate Charge	$Q_g$	$V_{GS} = 10V, V_{DS} = 15V, I_D = 25A$		22		$nC$
Total Gate Charge	$Q_g$	$V_{GS} = 4.5V, V_{DS} = 15V, I_D = 25A$		11		$nC$
Gate-Source Charge	$Q_{gs}$			5.4		
Gate-Drain Charge	$Q_{gd}$			5.5		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15V, V_{GEN} = 10V, R_G = 3\Omega, R_L = 15\Omega, I_D = 1.0A$	-	13.5		$ns$
Turn-Off Delay Time	$t_{d(off)}$		-	42		
Turn-On Rise Time	$t_r$		-	13		
Turn-On Fall Time	$t_f$		-	4		

## Typical Characteristics

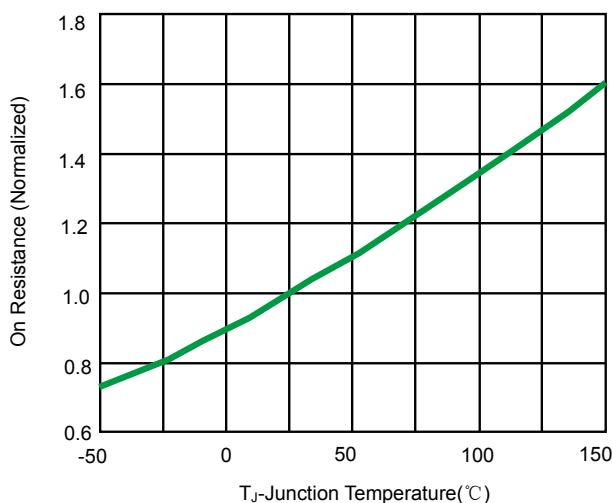


Fig 1. On Resistance vs. Junction Temperature

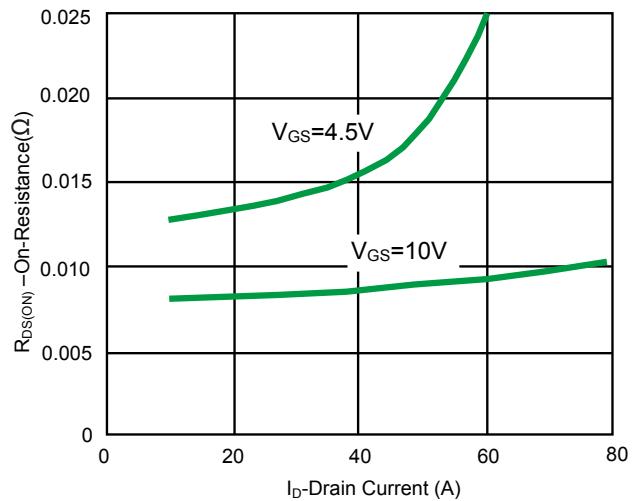


Fig 2. On-Resistance vs. Drain Current

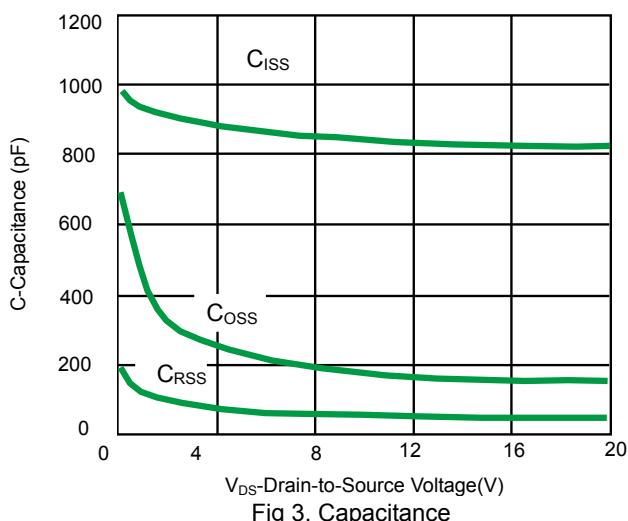


Fig 3. Capacitance

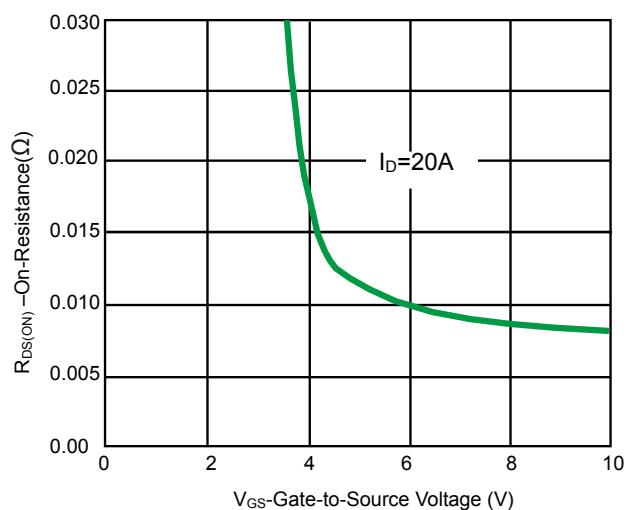


Fig 4. On-Resistance vs. Gate-to-Source Voltage

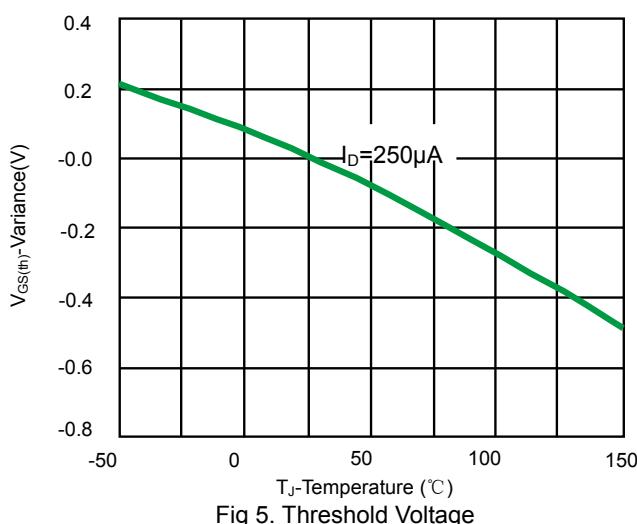


Fig 5. Threshold Voltage

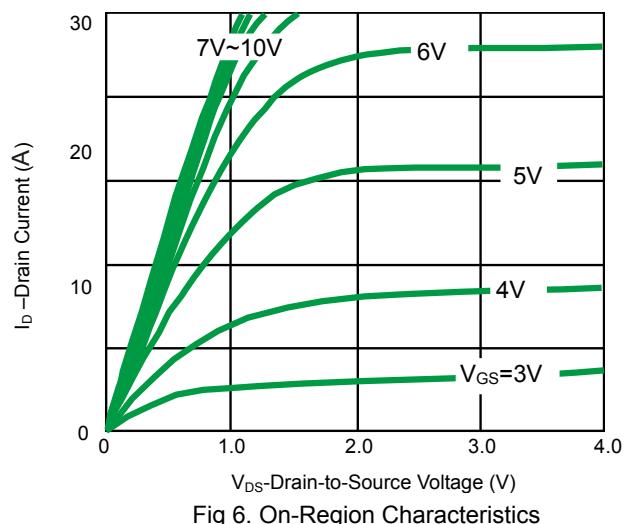


Fig 6. On-Region Characteristics

## N-Channel MOSFET

PNMDP30V60

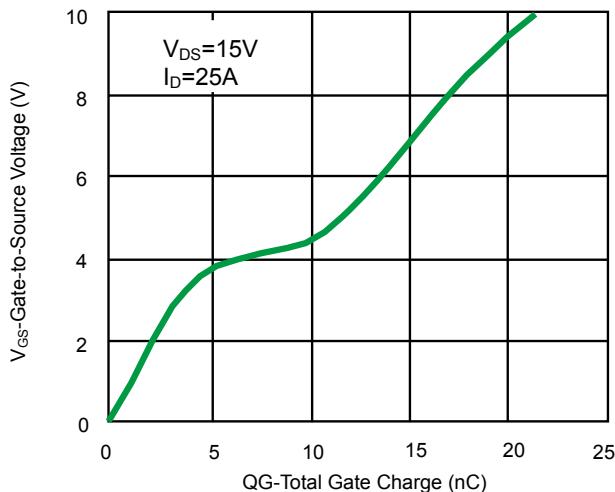


Fig 7. Gate Charge

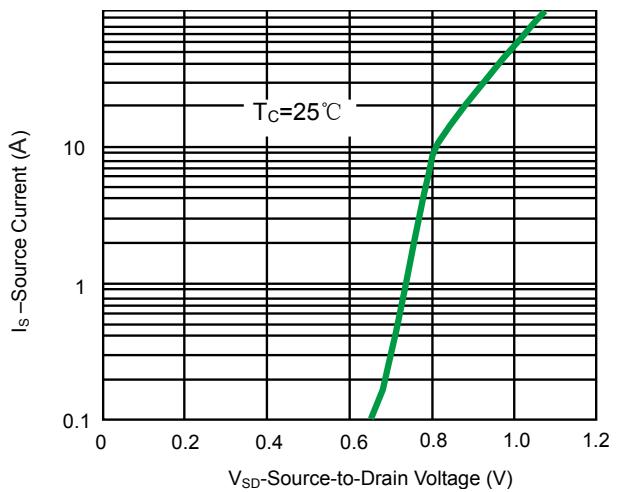


Fig 8. Source to Drain Diode Forward Voltage

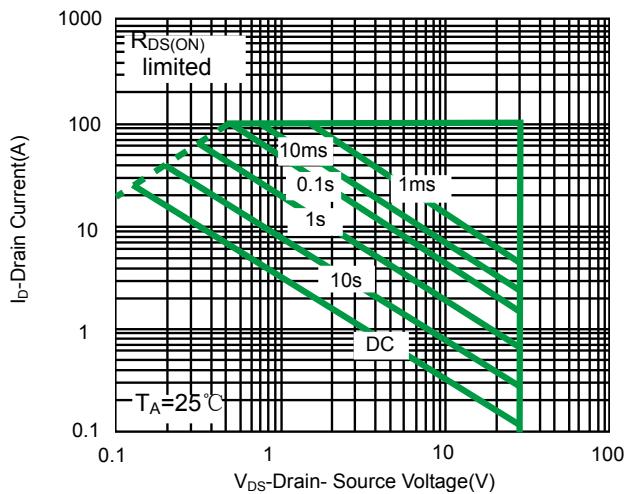


Fig 9. Maximum Forward Biased Safe Operating Area

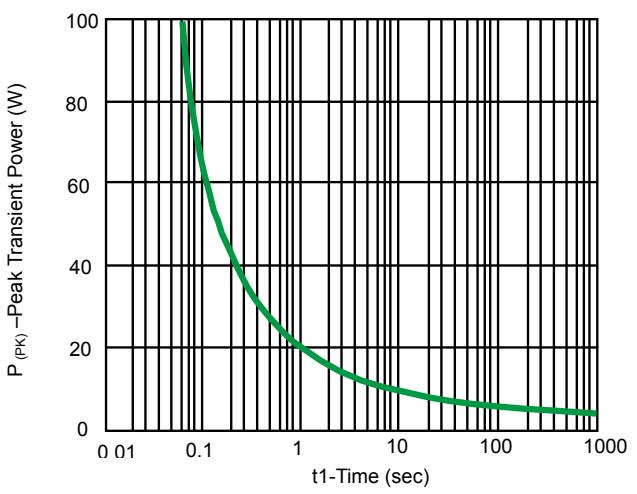


Fig 10. Single Pulse Maximum Power Dissipation

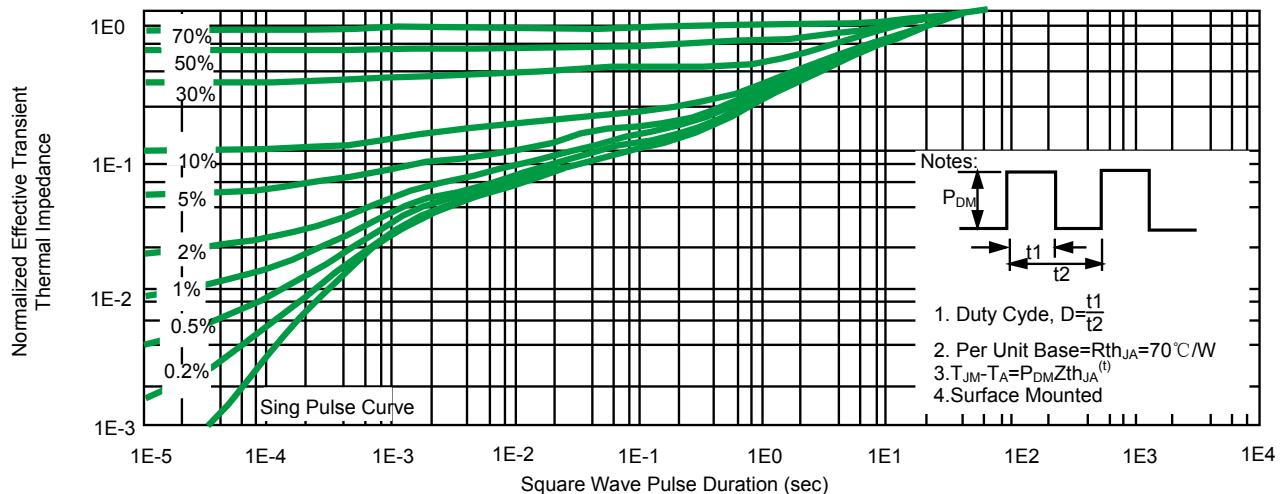
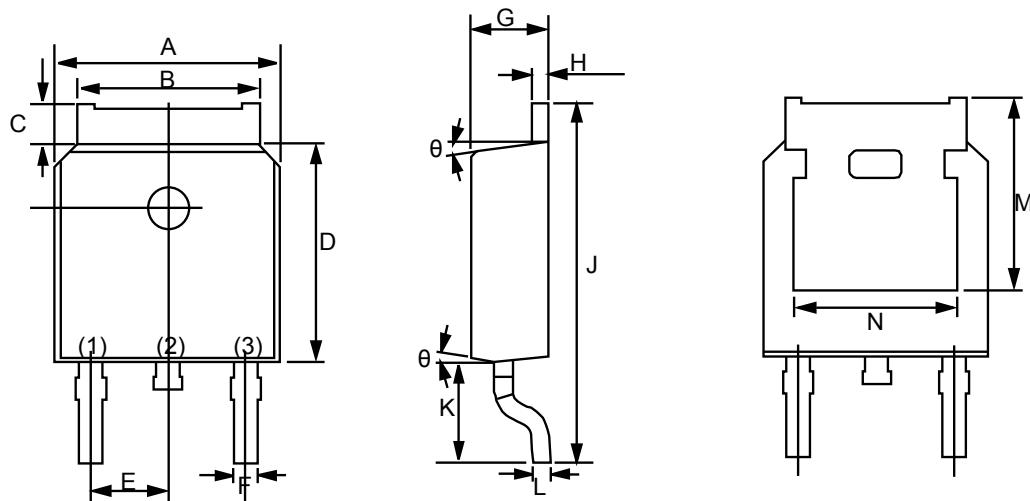


Fig 11. Normalized Thermal Transient Impedance, Junction-to-Ambient

## Product dimension(TO-252)



Dim	Millimeters		Inches	
	MIN	MAX	MIN	MAX
A	6.50	6.70	0.255	0.263
B	5.23	5.46	0.205	0.214
C	0.90	1.25	0.035	0.049
D	6.00	6.20	0.236	0.244
E	2.286BSC.		0.09BSC.	
F	0.72	0.85	0.028	0.033
G	2.20	2.38	0.086	0.093
H	0.47	0.58	0.018	0.022
J	9.90	10.30	0.389	0.405
K	2.90REF.		0.114REF.	
L	0.51BSC.		0.020BSC.	
M	5.30REF.		0.208REF.	
N	4.70	4.92	0.185	0.193
θ	5°	9°	5°	9°

**IMPORTANT NOTICE**

 and **Prisemi<sup>®</sup>** are registered trademarks of **Prisemi Electronics Co., Ltd (Prisemi)**, Prisemi reserves the right to make changes without further notice to any products herein. Prisemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does Prisemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in Prisemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. Prisemi does not convey any license under its patent rights nor the rights of others. The products listed in this document are designed to be used with ordinary electronic equipment or devices, Should you intend to use these products with equipment or devices which require an extremely high level of reliability and the malfunction of which would directly endanger human life (such as medical instruments, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices), please be sure to consult with our sales representative in advance.

Website: <http://www.prisemi.com>

For additional information, please contact your local Sales Representative.

©Copyright 2009, Prisemi Electronics

 **Prisemi<sup>®</sup>** is a registered trademark of Prisemi Electronics.

All rights are reserved.